STD4NK100Z

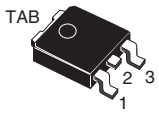
N-channel 1000 V, 5.6 Ω, 2.2 A SuperMESH™ Power MOSFET Zener-protected in DPAK package

Datasheet — preliminary data

Features

Order code	V_{DSS}	$R_{DS(on)}$max	I_D
STD4NK100Z	1000 V	< 6.8 Ω	2.2 A

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitance
- Very good manufacturing repeatability



DPAK

Applications

- Switching application
  - Automotive

Description

This device is an N-channel Zener-protected Power MOSFET developed using STMicroelectronics' SuperMESH™ technology, achieved through optimization of ST's well established strip-based PowerMESH™ layout. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Figure 1. Internal schematic diagram

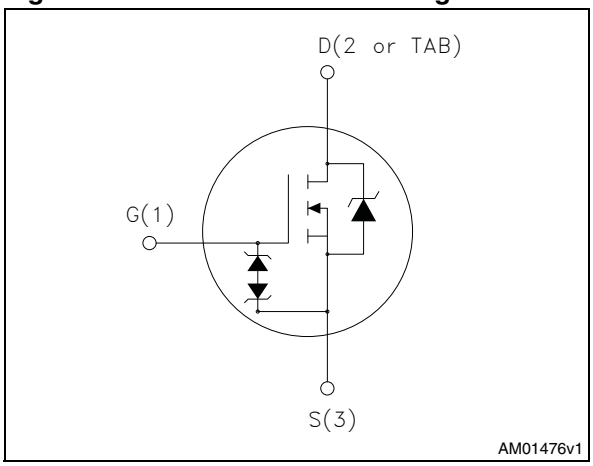


Table 1. Device summary

Order code	Marking	Package	Packaging
STD4NK100Z	4NK100Z	DPAK	Tape and reel

Contents

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	1000	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at T_C = 25 °C	2.2	A
I_D	Drain current (continuous) at T_C=100 °C	1	A
I_{DM} (1)	Drain current (pulsed)	8.8	A
P_{TOT}	Total dissipation at T_C = 25 °C	90	W
	Derating factor	0.72	W/°C
$V_{ESD(G-S)}$	Gate source ESD (HBM-C=100pF, R=1.5 kΩ)	3000	V
dv/dt (2)	Peak diode recovery voltage slope	TBD	V/ns
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150	°C

1. Pulse width limited by safe operating area
2. I_{SD} ≤2.2 A, di/dt ≤200 A/µs, V_{DD} ≤$V_{(BR)DSS}$, T_j ≤T_{JMAX}.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	1.39	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb max	50	°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_{JMAX})	2.2	A
E_{AS}	Single pulse avalanche energy (starting T_J=25 °C, I_D=I_{AR}, V_{DD}=50 V)	TBD	mJ

2 Electrical characteristics

(T_{CASE}=25 °C unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS}= 0	1000			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 1000 V, V_{DS} = 1000 V, Tc = 125 °C			1 50	µA µA
I_{GSS}	Gate body leakage current (V_{GS} = 0)	V_{GS} = ± 20 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 50 µA	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 1.1 A		5.6	6.8	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25 V, f=1 MHz, V_{GS}=0	-	601 53 12	-	pF pF pF
$C_{oss.\ eq}$ (1)	Equivalent output capacitance	V_{GS}=0, V_{DS} =0 V to 800 V	-	TBD	-	pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Off-voltage rise time Fall time	V_{DD}=500 V, I_D= 1.25 A, R_G=4.7 Ω, V_{GS}=10 V (see *Figure 4*)	-	15 7.5 32 39	-	ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}=800 V, I_D = 2.5 A V_{GS} =10 V (see *Figure 3*)	-	18 3.6 9.2	-	nC nC nC

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		2.2	A
I_{SDM} (1)	Source-drain current (pulsed)		-		8.8	A
V_{SD} (2)	Forward on voltage	I_{SD}= 2.2 A, V_{GS}=0	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}= 2.5 A, di/dt = 100 A/µs, V_{DD}=100 V (see *Figure 2*)	-	584 2.3 8		ns µC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}= 2.5 A, di/dt = 100 A/µs, V_{DD}=100 V, T_j=150 °C (see *Figure 2*)	-	628 2.5 8.1		ns µC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 µs, duty cycle 1.5%

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	Igs=± 1 mA (open drain)	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

3 Test circuits

Figure 2. Switching times test circuit for resistive load

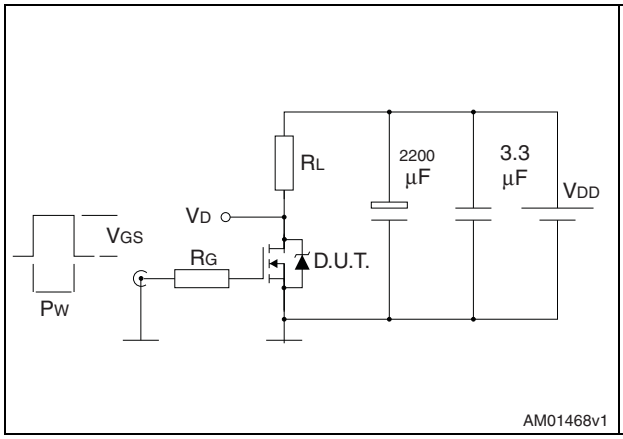


Figure 3. Gate charge test circuit

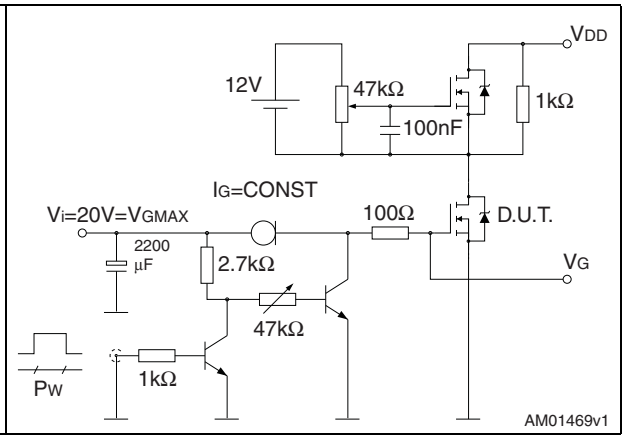


Figure 4. Test circuit for inductive load switching and diode recovery times

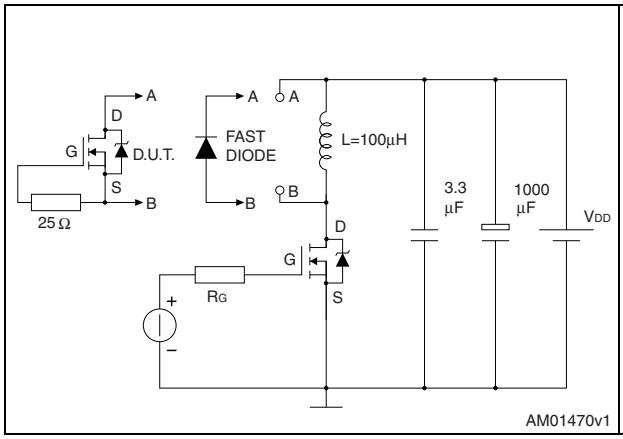


Figure 5. Unclamped inductive load test circuit

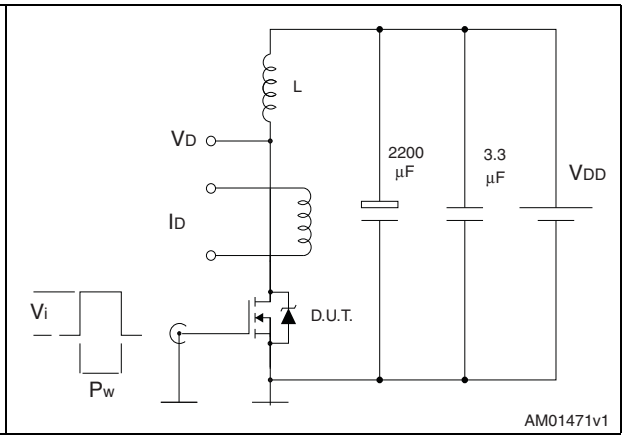


Figure 6. Unclamped inductive waveform

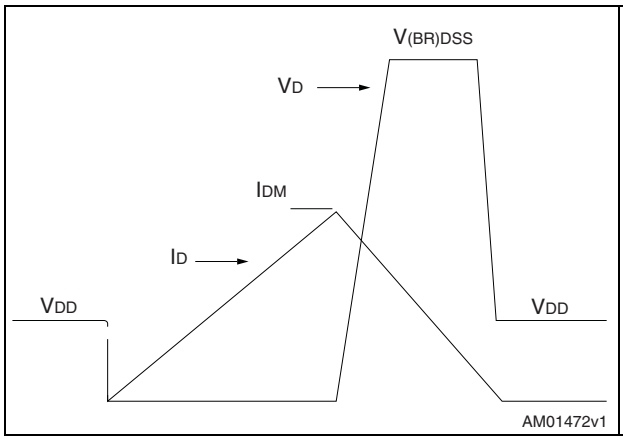
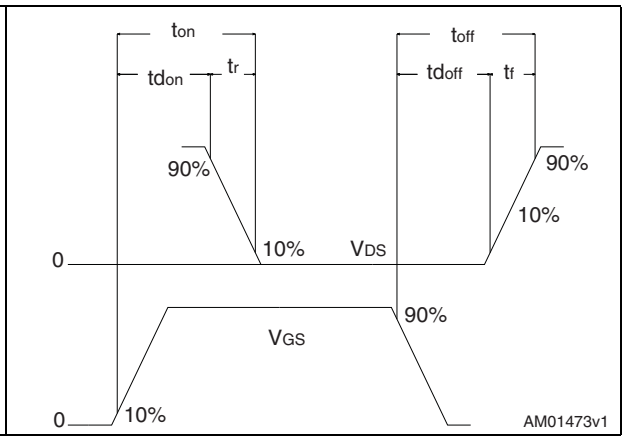


Figure 7. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 8. DPAK (TO-252) drawing

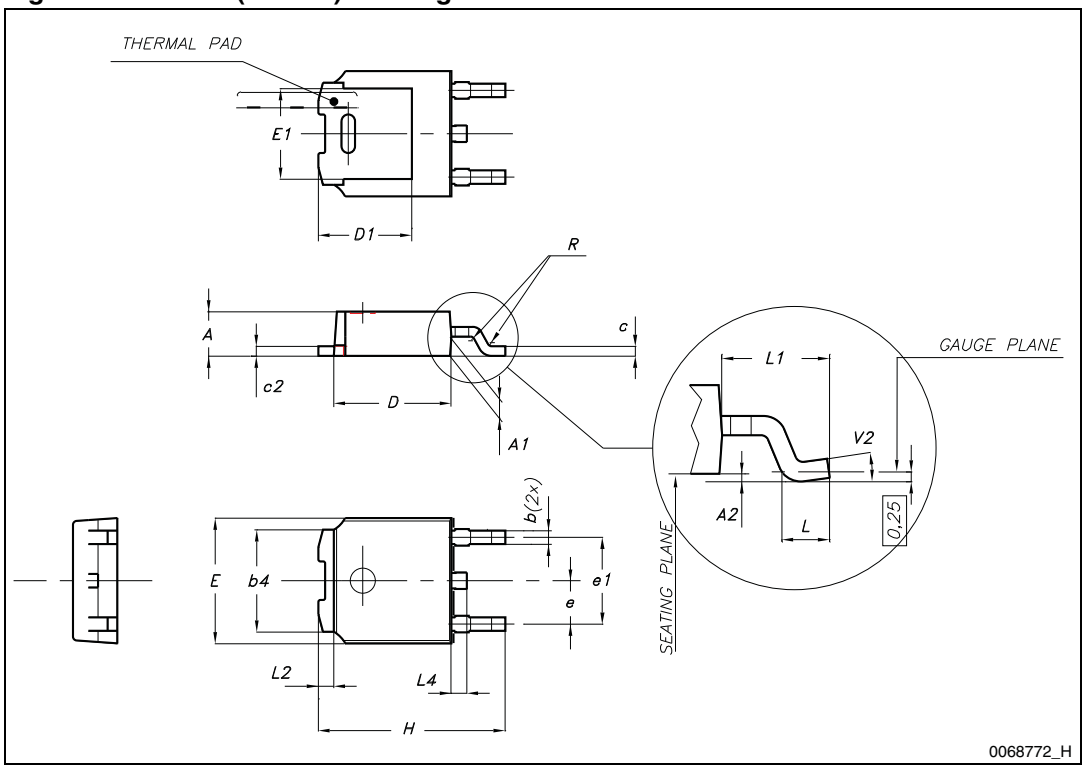
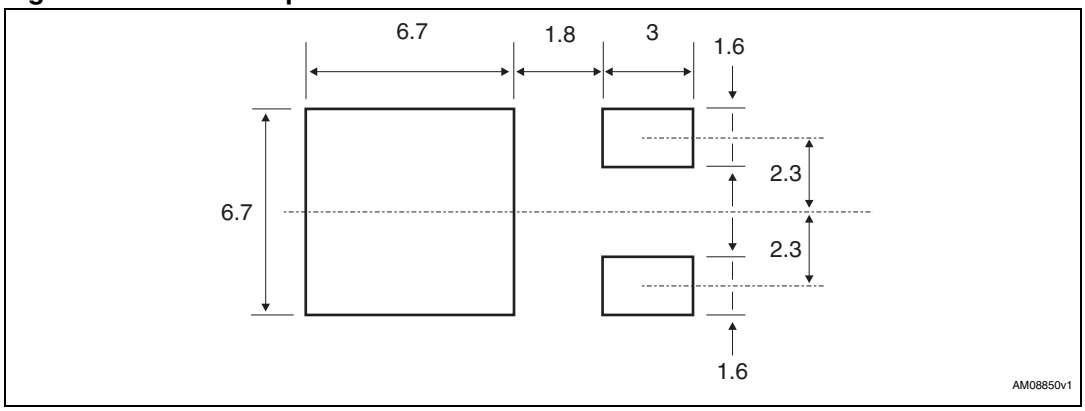


Figure 9. DPAK footprint[a]



a. All dimensions are in millimeters

5 Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Figure 10. Tape for DPAK (TO-252)

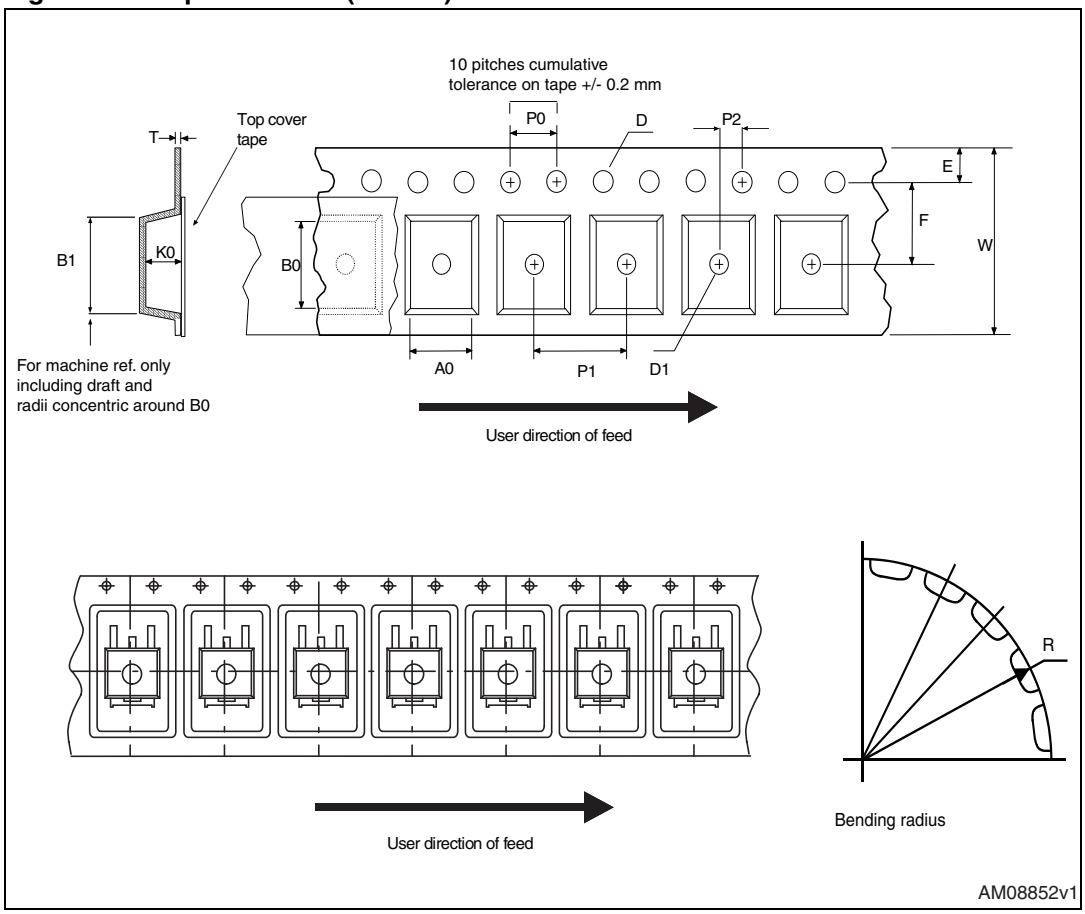
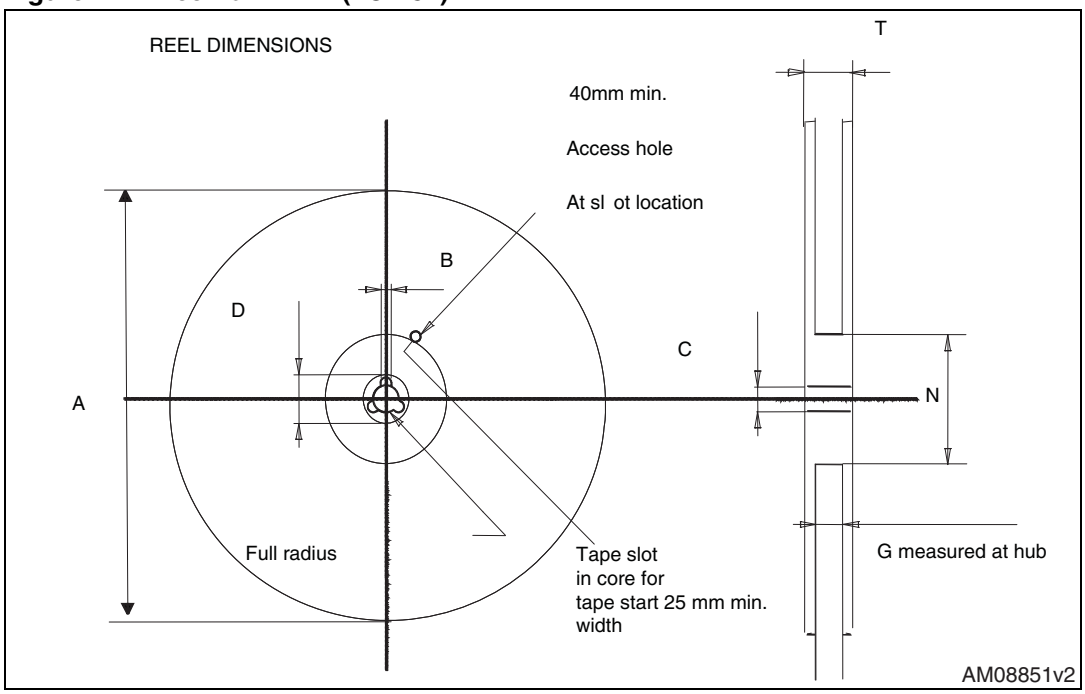


Figure 11. Reel for DPAK (TO-252)



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
02-mar-2012	1	First release.

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